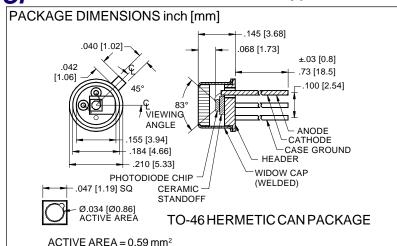
PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive **Isolated Type PDB-C100** DETECTORS INC.





FEATURES

- High speed
- Low capacitance
- Isolated chip
- Low dark current

DESCRIPTION

The PDB-C100 is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive & fiberoptic applications. Packaged in a hermetic TO-46 metal can with a flat window and isolated $\begin{array}{ll} \mbox{ground lead.} \\ \mbox{RATING} & \mbox{(TA=25°C unless otherwise noted)} \end{array}$

APPLICATIONS

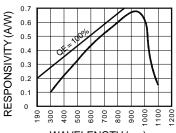
- Fiber optic
- Industrial controls
- Laser detection
- Particle detection

ABSOLUTE MAXIMUM

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-55	+150	°C
T _o	Operating Temperature Range	-40	+125	°C
T _s	Soldering Temperature*		+240	°C
I _L	Light Current		0.5	mA

^{*1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

(171-20 0 difference)								
SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS		
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	9	11		μΑ		
I _D	Dark Current	H = 0, V _R = 15 V		1.0	2.0	nA		
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$.50	5		GΩ		
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃		
C _J	Junction Capacitance	H = 0, V _R = 15 V**		5	7	pF		
λ range	Spectral Application Range	Spot Scan	400		1150	nm		
λр	Spectral Response - Peak	Spot Scan		850		nm		
V _{BR}	Breakdown Voltage	I = 10 μA	100	125		V		
NEP	Noise Equivalent Power	V _R = 15 V @ Peak		40x10 ⁻¹⁵		W/√Hz		
tr	Response Time	RL = 50 Ω V _p = 15 V		3		nS		